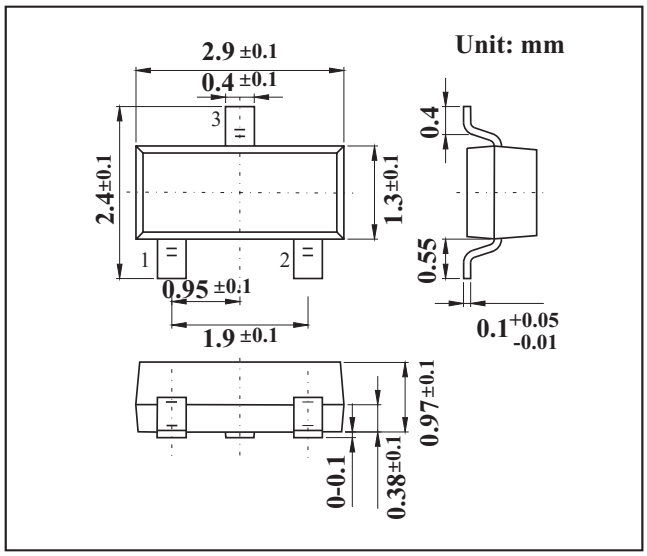
SOT-23 Plastic-Encapsulate MOSFETS

FEATURE

- Low on-resistance
- Fast switching speed
- Low voltage drive makes this device ideal for
- Portable equipment
- Easily designed drive circuits
- Easy to parallel
- N-channel MOSFET

MECHANICAL DATA

- Case style:SOT-23molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	60	V
Gate-source Voltage		V_{GS}	±20	V
Drain Current	T_A=25℃	I_D	3	A
	T_A=70℃		2.4	
Pulsed Drain Current [A]		I_{DM}	12	A
Total Power Dissipation @ T_C=25℃		P_D	1.2	W
Thermal Resistance Junction-to-Ambient [B]		$R_{\theta JA}$	105	℃/ W
Junction and Storage Temperature Range		T_J ,T_{STG}	-55～+150	℃

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}= 0V, I_D=250μA	60			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=60V,V_{GS}=0V			1	μA
Gate-Body Leakage Current	I_{GSS1}	V_{GS}= ±20V, V_{DS}=0V			±100	nA
	I_{GSS2}	V_{GS}= ±10V, V_{DS}=0V			±50	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}= V_{GS}, I_D=250μA	1.0	1.7	2.0	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}= 10V, I_D=3A		58	100	mΩ
		V_{GS}= 4.5V, I_D=1.5A		70	110	
Diode Forward Voltage	V_{SD}	I_S=3.0A,V_{GS}=0V		0.8	1.2	V
Maximum Body-Diode Continuous Current	I_S				3.0	A
Dynamic Parameters						
Input Capacitance	C_{iss}	V_{DS}=30V,V_{GS}=0V,f=1MHZ		330		pF
Output Capacitance	C_{oss}			90		
Reverse Transfer Capacitance	C_{rss}			17		
Switching Parameters						
Total Gate Charge	Q_g	V_{GS}=10V,V_{DS}=30V,I_D=3.0A		5.1		nC
Gate-Source Charge	Q_{gs}			1.3		
Gate-Drain Charge	Q_{gd}			1.7		
Turn-on Delay Time	$t_{D(on)}$	V_{GS}=10V,V_{DD}=30V, I_D=1.5A,R_L=1Ω R_{GEN}=3Ω		13		ns
Turn-on Rise Time	t_r			51		
Turn-off Delay Time	$t_{D(off)}$			19		
Turn-off fall Time	t_f			12		

A. Pulse Test: Pulse Width≤300us,Duty cycle ≤2%
B. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch

RATINGS AND CHARACTERISTIC CURVES

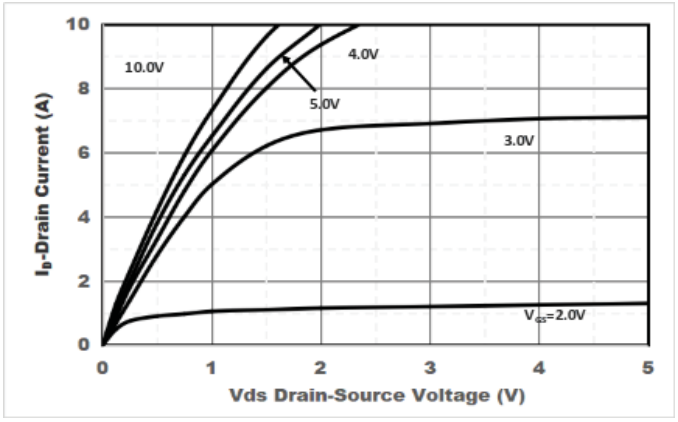


Figure1. Output Characteristics

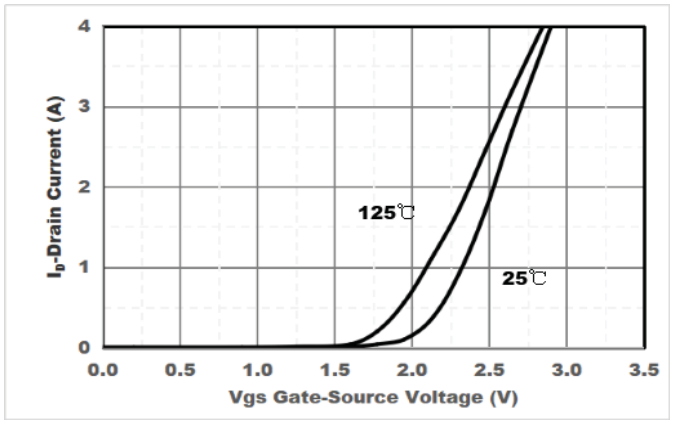


Figure2. Transfer Characteristics

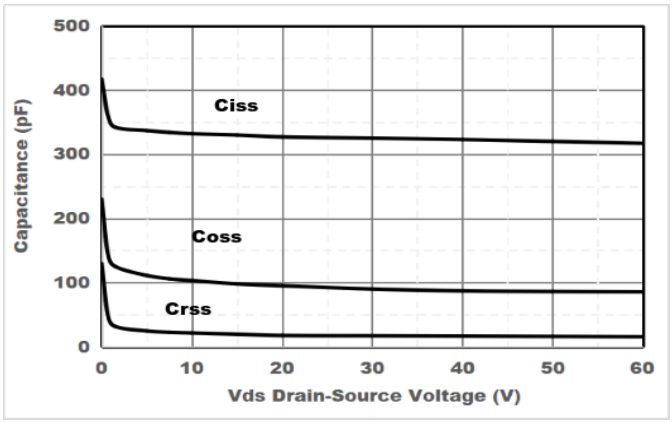


Figure3. Capacitance Characteristics

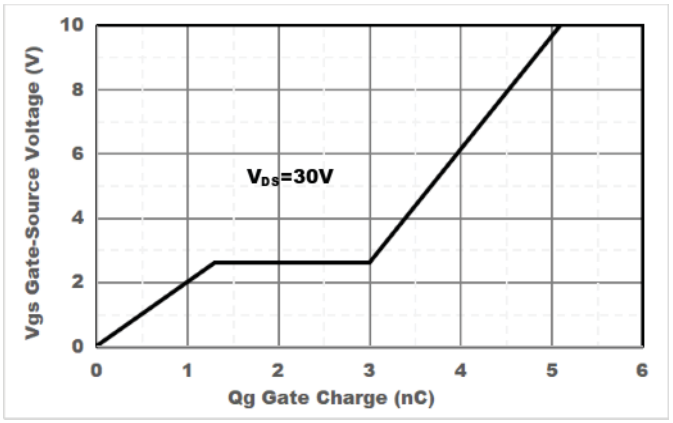


Figure4. Gate Charge

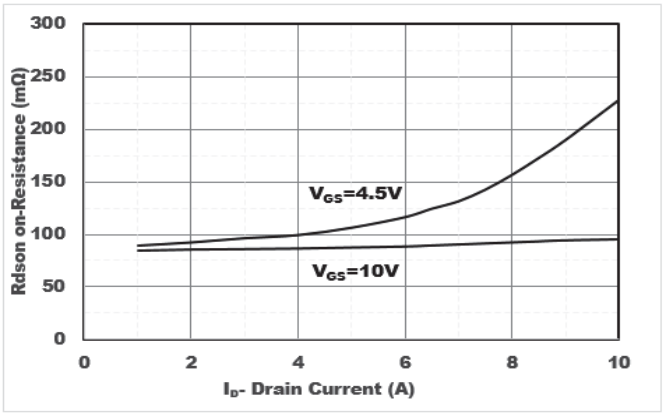


Figure5. Drain-Source on Resistance

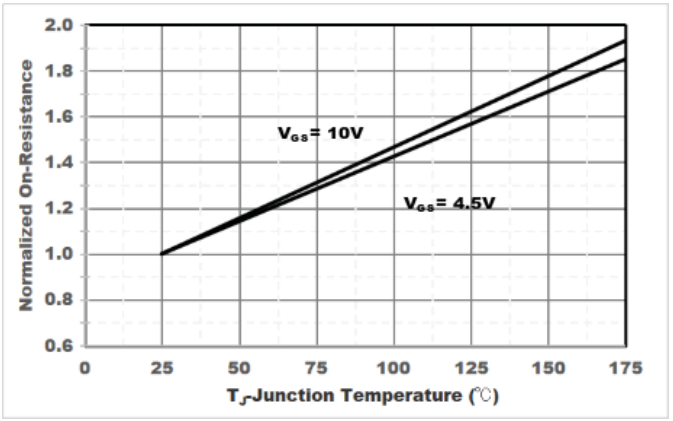


Figure6. Drain-Source on Resistance

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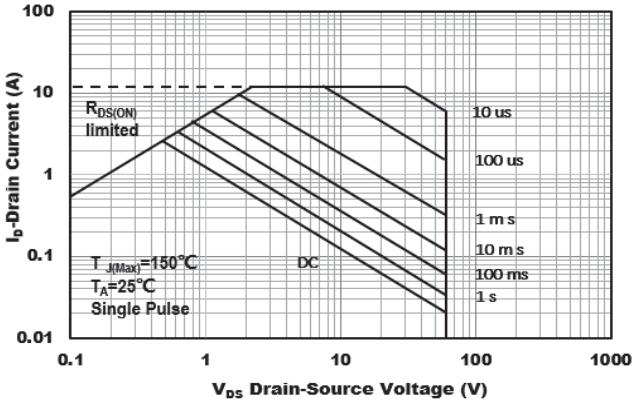

Figure7. Safe Operation Area

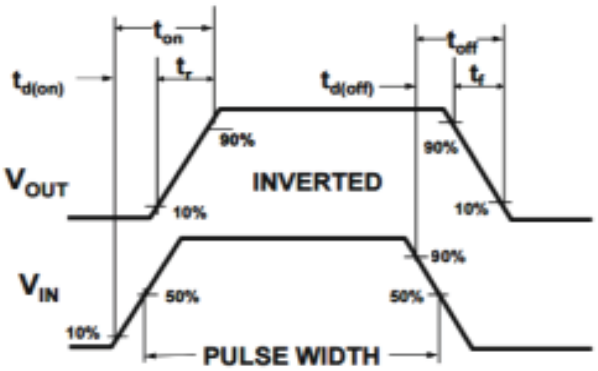

Figure8. Switching wave